

Yoshiaki Nakamura

List of Publications by Year in descending order

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184
papers

2,724
citations

186265

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243625

44
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186
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186
docs citations

186
times ranked

2010
citing authors

#	ARTICLE	IF	CITATIONS
1	Anomalous reduction of thermal conductivity in coherent nanocrystal architecture for silicon thermoelectric material. <i>Nano Energy</i> , 2015, 12, 845-851.	16.0	150
2	An Approach to Ideal Semiconductor Electrodes for Efficient Photoelectrochemical Reduction of Carbon Dioxide by Modification with Small Metal Particles. <i>Journal of Physical Chemistry B</i> , 1998, 102, 974-980.	2.6	144
3	Observation of the quantum-confinement effect in individual Ge nanocrystals on oxidized Si substrates using scanning tunneling spectroscopy. <i>Applied Physics Letters</i> , 2005, 87, 133119.	3.3	112
4	Quantum-confinement effect in individual Ge _{1-x} Sn _x quantum dots on Si(111) substrates covered with ultrathin SiO ₂ films using scanning tunneling spectroscopy. <i>Applied Physics Letters</i> , 2007, 91, .	3.3	82
5	Self-Consistent Density Functional Calculation of Field Emission Currents from Metals. <i>Physical Review Letters</i> , 2000, 85, 1750-1753.	7.8	74
6	Methodology of Thermoelectric Power Factor Enhancement by Controlling Nanowire Interface. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 37709-37716.	8.0	72
7	Phonon transport control by nanoarchitecture including epitaxial Ge nanodots for Si-based thermoelectric materials. <i>Scientific Reports</i> , 2015, 5, 14490.	3.3	71
8	Nanostructure design for drastic reduction of thermal conductivity while preserving high electrical conductivity. <i>Science and Technology of Advanced Materials</i> , 2018, 19, 31-43.	6.1	69
9	A reproducible method to fabricate atomically sharp tips for scanning tunneling microscopy. <i>Review of Scientific Instruments</i> , 1999, 70, 3373-3376.	1.3	59
10	Self-organized formation and self-repair of a two-dimensional nanoarray of Ge quantum dots epitaxially grown on ultrathin SiO ₂ -covered Si substrates. <i>Nanotechnology</i> , 2010, 21, 095305.	2.6	58
11	Epitaxial Growth of High Quality Ge Films on Si(001) Substrates by Nanocontact Epitaxy. <i>Crystal Growth and Design</i> , 2011, 11, 3301-3305.	3.0	48
12	Nanoscale Imaging of Electronic Surface Transport Probed by Atom Movements Induced by Scanning Tunneling Microscope Current. <i>Physical Review Letters</i> , 2002, 89, 266805.	7.8	46
13	Independent control of electrical and heat conduction by nanostructure designing for Si-based thermoelectric materials. <i>Scientific Reports</i> , 2016, 6, 22838.	3.3	45
14	Ultimate Confinement of Phonon Propagation in Silicon Nanocrystalline Structure. <i>Physical Review Letters</i> , 2018, 120, 045901.	7.8	45
15	Quantum fluctuation of tunneling current in individual Ge quantum dots induced by a single-electron transfer. <i>Applied Physics Letters</i> , 2007, 90, 153104.	3.3	44
16	Epitaxial growth of ultrahigh density Ge _{1-x} Sn _x quantum dots on Si (111) substrates by codeposition of Ge and Sn on ultrathin SiO ₂ films. <i>Journal of Applied Physics</i> , 2007, 102, 124302.	2.5	43
17	Formation of ultrahigh density and ultrasmall coherent FeSi_2 nanodots on Si (111) substrates using Si and Fe codeposition method. <i>Journal of Applied Physics</i> , 2006, 100, 044313.	2.5	40
18	Thermoelectric power factor enhancement based on carrier transport physics in ultimately phonon-controlled Si nanostructures. <i>Materials Today Energy</i> , 2019, 13, 56-63.	4.7	39

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19	Formation of strained iron silicide nanodots by Fe deposition on Si nanodots on oxidized Si (111) surfaces. <i>Physical Review B</i> , 2005, 72, .	3.2	36
20	High Thermoelectric Power Factor Realization in Si-Rich SiGe/Si Superlattices by Super-Controlled Interfaces. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 25428-25434.	8.0	36
21	Quantum confinement observed in Ge nanodots on an oxidized Si surface. <i>Physical Review B</i> , 2006, 73, .	3.2	35
22	Nanocontact heteroepitaxy of thin GaSb and AlGaSb films on Si substrates using ultrahigh-density nanodot seeds. <i>Nanotechnology</i> , 2011, 22, 265301.	2.6	33
23	In situ scanning tunneling microscopic study of polymerization of C60 clusters induced by electron injection from the probe tips. <i>Applied Physics Letters</i> , 2000, 77, 2834-2836.	3.3	30
24	Low thermal conductivity in single crystalline epitaxial germanane films. <i>Applied Physics Express</i> , 2020, 13, 055503.	2.4	30
25	Carrier and phonon transport control by domain engineering for high-performance transparent thin film thermoelectric generator. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	30
26	Cluster reactions in C60 films induced by electron injection from a scanning tunneling microscope tip. <i>Surface Science</i> , 2003, 528, 151-155.	1.9	29
27	Photoluminescence of Ge ^δ -Si structures grown on oxidized Si surfaces. <i>Applied Physics Letters</i> , 2006, 88, 121919.	3.3	29
28	Self-Assembled Epitaxial Growth of High Density FeSi ₂ Nanodots on Si (001) and Their Spatially Resolved Optical Absorption Properties. <i>Crystal Growth and Design</i> , 2008, 8, 3019-3023.	3.0	29
29	Formation of ultrahigh density Ge nanodots on oxidized Ge/Si(111) surfaces. <i>Journal of Applied Physics</i> , 2004, 95, 5014-5018.	2.5	28
30	Enhanced thermoelectric performance of Ga-doped ZnO film by controlling crystal quality for transparent thermoelectric films. <i>Thin Solid Films</i> , 2018, 666, 185-190.	1.8	28
31	Formation and optical properties of GaSb quantum dots epitaxially grown on Si substrates using an ultrathin SiO ₂ film technique. <i>Journal of Applied Physics</i> , 2009, 105, .	2.5	27
32	Resistive switching memory performance in oxide hetero-nanocrystals with well-controlled interfaces. <i>Science and Technology of Advanced Materials</i> , 2020, 21, 195-204.	6.1	27
33	Nonthermal decomposition of C60 polymers induced by tunneling electron injection. <i>Applied Physics Letters</i> , 2004, 85, 5242-5244.	3.3	26
34	Influence of growth and annealing conditions on photoluminescence of Ge/Si layers grown on oxidized Si surfaces. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 136004.	1.8	26
35	Photoluminescence of Si layers grown on oxidized Si surfaces. <i>Journal of Applied Physics</i> , 2007, 101, 033532.	2.5	26
36	Giant Enhancement of Seebeck Coefficient by Deformation of Silicene Buckled Structure in Calcium-Intercalated Layered Silicene Film. <i>Advanced Materials Interfaces</i> , 2022, 9, 2101752.	3.7	26

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37	Observation of the quantum-confinement effect in individual FeSi_2 nanoislands epitaxially grown on Si (111) surfaces using scanning tunneling spectroscopy. <i>Applied Physics Letters</i> , 2006, 89, 123104.	3.3	24
38	Diffusion of chlorine atoms on Si(111)-(7 \times 7) surface enhanced by electron injection from scanning tunneling microscope tips. <i>Surface Science</i> , 2001, 487, 127-134.	1.9	23
39	Phonon transport in the nano-system of Si and SiGe films with Ge nanodots and approach to ultralow thermal conductivity. <i>Nanoscale</i> , 2021, 13, 4971-4977.	5.6	22
40	Photoluminescence from Si-capped GeSn nanodots on Si substrates formed using an ultrathin SiO ₂ film technique. <i>Journal of Applied Physics</i> , 2009, 106, 014309.	2.5	21
41	Defect-related light emission in the 1.4 μm –1.7 μm range from Si layers at room temperature. <i>Journal of Applied Physics</i> , 2009, 105, .	2.5	20
42	Embedded-ZnO Nanowire Structure for High-Performance Transparent Thermoelectric Materials. <i>Journal of Electronic Materials</i> , 2017, 46, 3020-3024.	2.2	20
43	Anomalous enhancement of thermoelectric power factor by thermal management with resonant level effect. <i>Journal of Materials Chemistry A</i> , 2021, 9, 4851-4857.	10.3	20
44	Thermoelectric Si _{1-x} Ge _x and Ge epitaxial films on Si(001) with controlled composition and strain for group IV element-based thermoelectric generators. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	19
45	STM Images Apparently Corresponding to a Stable Structure: Considerable Fluctuation of a Phase Boundary of the Si(111)-(3 \times 3)-Ag Surface. <i>Physical Review Letters</i> , 2001, 87, 156102.	7.8	18
46	Hopping motion of chlorine atoms on Si(100)-(2 \times 1) surfaces induced by carrier injection from scanning tunneling microscope tips. <i>Surface Science</i> , 2003, 531, 68-76.	1.9	17
47	Strength distribution of titania ceramics after high-voltage screening. <i>Journal of Materials Science</i> , 1996, 31, 3419-3425.	3.7	16
48	Spreading effects in surface reactions induced by tunneling current injection from an STM tip. <i>Surface Science</i> , 2003, 528, 110-114.	1.9	16
49	Fourier-transform photoabsorption spectroscopy of quantum-confinement effects in individual GeSn nanodots. <i>Applied Physics Letters</i> , 2009, 94, 093104.	3.3	16
50	Molecular dynamics study of deposition mechanism of cubic boron nitride. <i>Science and Technology of Advanced Materials</i> , 2001, 2, 349-356.	6.1	15
51	Dislocation confinement in the growth of Na flux GaN on metalorganic chemical vapor deposition-GaN. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	15
52	Thermoelectric Properties of Epitaxial FeSi_2 Thin Films on Si(111) and Approach for Their Enhancement. <i>Journal of Electronic Materials</i> , 2017, 46, 3235-3241.	2.2	15
53	Significant reduction in the thermal conductivity of Si-substituted $\text{Fe}_{1-x}\text{Si}_x$ epilayers. <i>Physical Review B</i> , 2019, 99, .	2.2	15
54	Methodology of Thermoelectric Power Factor Enhancement by Nanoscale Thermal Management in Bulk SiGe Composites. <i>ACS Applied Energy Materials</i> , 2020, 3, 1235-1241.	5.1	14

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55	Chlorine atom diffusion on Si(111)-(7 \times 7) surface enhanced by hole injection from scanning tunneling microscope tips. <i>Surface Science</i> , 2002, 497, 166-170.	1.9	13
56	Structural change of radiation defects in graphite crystals induced by STM probing. <i>Applied Physics A: Materials Science and Processing</i> , 2002, 74, 311-316.	2.3	13
57	Desorption of chlorine atoms on Si(111)-(7 \times 7) surfaces induced by hole injection from scanning tunneling microscope tips. <i>Surface Science</i> , 2007, 601, 2189-2193.	1.9	13
58	Fabrication of Si Thermoelectric Nanomaterials Containing Ultrasmall Epitaxial Ge Nanodots with an Ultrahigh Density. <i>Journal of Electronic Materials</i> , 2015, 44, 2015-2020.	2.2	13
59	Fabrication of Carrier-Doped Si Nanoarchitecture for Thermoelectric Material by Ultrathin SiO ₂ Film Technique. <i>Journal of Electronic Materials</i> , 2016, 45, 1914-1920.	2.2	13
60	Arbitrary cross-section SEM-cathodoluminescence imaging of growth sectors and local carrier concentrations within micro-sampled semiconductor nanorods. <i>Nature Communications</i> , 2016, 7, 10609.	12.8	13
61	High thermoelectric performance in high crystallinity epitaxial Si films containing silicide nanodots with low thermal conductivity. <i>Applied Physics Letters</i> , 2019, 115, 182104.	3.3	13
62	Atomic and electronic structure of the Si(111)- $\sqrt{3}\times\sqrt{3}$ -Ag surface reexamined using first-principles calculations. <i>Science and Technology of Advanced Materials</i> , 2000, 1, 167-172.	6.1	12
63	Ultrathin-body Ge-on-insulator wafers fabricated with strongly bonded thin Al ₂ O ₃ /SiO ₂ hybrid buried oxide layers. <i>Applied Physics Express</i> , 2014, 7, 086501.	2.4	12
64	Low thermal conductivity of thermoelectric Fe ₂ VAl films. <i>Applied Physics Express</i> , 2017, 10, 115802.	2.4	12
65	Thermoelectric properties of single-phase full-Heusler alloy Fe ₂ TiSi films with D _{3h} -type disordering. <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	12
66	Measurements of local optical properties of Si-doped GaAs(110) surfaces using modulation scanning tunneling microscope cathodoluminescence spectroscopy. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 195.	1.3	11
67	Fabrication of bonded GeOI substrates with thin Al ₂ O ₃ /SiO ₂ buried oxide layers. <i>Solid-State Electronics</i> , 2013, 83, 42-45.	1.4	11
68	Epitaxial multilayers of $\sqrt{2}\times\sqrt{2}$ -FeSi ₂ nanodots/Si for Si-based nanostructured electronic materials. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, 041402.	2.1	11
69	Thermal Conductivity Measurement of Thermoelectric Thin Films by a Versatility-Enhanced 2π Method. <i>Journal of Electronic Materials</i> , 2017, 46, 3089-3096.	2.2	11
70	Resistive switching at the high quality metal/insulator interface in Fe ₃ O ₄ /SiO ₂ /FeSi ₂ /Si stacking structure. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	11
71	Bottom-Up Surface Synthesis of Two-Dimensional Graphene Nanoribbon Networks and Their Thermoelectric Properties. <i>Chemistry - an Asian Journal</i> , 2019, 14, 4400-4407.	3.3	11
72	Nanostructure design for high performance thermoelectric materials based on anomalous Nernst effect using metal/semiconductor multilayer. <i>Applied Physics Express</i> , 2021, 14, 075002.	2.4	11

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73	Polymerization and depolymerization of fullerenes induced by hole injection from scanning tunneling microscope tips. <i>Surface Science</i> , 2007, 601, 5207-5211.	1.9	10
74	Luminescence at 1.5 μm from Si/GeSn nanodot/Si structures. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 035304.	2.8	10
75	Cross-sectional X-ray microdiffraction study of a thick AlN film grown on a trench-patterned AlN/ Al_2O_3 template. <i>Journal of Crystal Growth</i> , 2013, 381, 37-42.	1.5	10
76	Epitaxial iron oxide nanocrystals with memory function grown on Si substrates. <i>Applied Physics Express</i> , 2016, 9, 055508.	2.4	10
77	An advanced 2D method enabling thermal conductivity measurement for various sample thicknesses: From thin films to bulk materials. <i>Journal of Applied Physics</i> , 2020, 128, 015102.	2.5	10
78	Fourier transform photoabsorption spectroscopy based on scanning tunneling microscopy. <i>Journal of Applied Physics</i> , 2007, 102, .	2.5	9
79	Control of epitaxial growth of Fe-based nanocrystals on Si substrates using well-controlled nanometer-sized interface. <i>Journal of Applied Physics</i> , 2014, 115, 044301.	2.5	9
80	Effect of Fe δ nonstoichiometry on electrical and thermoelectric properties of Fe ₂ VAl films. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 040306.	1.5	9
81	Impact of metal silicide nanocrystals on the resistance ratio in resistive switching of epitaxial Fe ₃ O ₄ films on Si substrates. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	9
82	Thermoelectric power factor enhancement of calcium-intercalated layered silicene by introducing metastable phase. <i>Applied Physics Express</i> , 2021, 14, 115505.	2.4	9
83	Quantum-Size Effect in Uniform Ge δ Sn Alloy Nanodots Observed by Photoemission Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L1176.	1.5	8
84	The origin of spectral distortion in electric field modulation spectroscopy based on scanning tunneling microscopy. <i>Surface Science</i> , 2007, 601, 5300-5303.	1.9	8
85	Spatial resolution of imaging contaminations on the GaAs surface by scanning tunneling microscope-cathodoluminescence spectroscopy. <i>Applied Surface Science</i> , 2008, 254, 7737-7741.	6.1	8
86	Fe ₃ Si nanodots epitaxially grown on Si(111) substrates using ultrathin SiO ₂ film technique. <i>Thin Solid Films</i> , 2011, 519, 8512-8515.	1.8	8
87	Electrical Characterization of Wafer-Bonded Germanium-on-Insulator Substrates Using a Four-Point-Probe Pseudo-Metal δ Oxide δ Semiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DA14.	1.5	8
88	Vertical dislocations in Ge films selectively grown in submicron Si windows of patterned substrates. <i>Thin Solid Films</i> , 2012, 520, 3245-3248.	1.8	8
89	Influence of nanometer-sized interface on reaction of iron nanocrystals epitaxially grown on silicon substrates with oxygen gas. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	8
90	Microscopic crystalline structure of a thick AlN film grown on a trench-patterned AlN/ Al_2O_3 template. <i>Journal of Crystal Growth</i> , 2015, 411, 38-44.	1.5	8

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91	Thermoelectric properties of epitaxial Ge thin films on Si(001) with strong crystallinity dependence. Applied Physics Express, 2018, 11, 111301.	2.4	8
92	Heat transport through propagon-phonon interaction in epitaxial amorphous-crystalline multilayers. Communications Physics, 2021, 4, .	5.3	8
93	Title is missing!. Journal of Materials Science, 1999, 34, 4233-4237.	3.7	7
94	Evidence of negative leaders prior to fast rise ICC pulses of upward lightning. Journal of Atmospheric Electricity, 2009, 29, 13-21.	0.3	7
95	Scanning tunneling microscope-cathodoluminescence measurement of the GaAs/AlGaAs heterostructure. Journal of Vacuum Science & Technology B, 2009, 27, 1874.	1.3	7
96	Structural change of direct silicon bonding substrates by interfacial oxide out-diffusion annealing. Thin Solid Films, 2010, 518, S147-S150.	1.8	7
97	Luminescence properties of Si-capped FeSi_2 nanodots epitaxially grown on Si(001) and (111) substrates. Journal of Applied Physics, 2014, 115, .	2.5	7
98	Resistive switching characteristics of isolated core-shell iron oxide/germanium nanocrystals epitaxially grown on Si substrates. Applied Physics Letters, 2018, 112, .	3.3	7
99	Structural Analysis of Si-Based Nanodot Arrays Self-Organized by Selective Etching of SiGe/Si Films. Japanese Journal of Applied Physics, 2011, 50, 08LB11.	1.5	7
100	Low thermal conductivity of complex thermoelectric barium silicide film epitaxially grown on Si. Applied Physics Letters, 2021, 119, .	3.3	7
101	Manipulating Ge quantum dots on ultrathin $\text{Si}_x\text{Ge}_{1-x}$ oxide films using scanning tunneling microscope tips. Surface Science, 2006, 600, 3456-3460.	1.9	6
102	Electric field modulation nanospectroscopy for characterization of individual FeSi_2 nanodots. Journal of Applied Physics, 2008, 104, .	2.5	6
103	Formation and Magnetic Properties of Ultrahigh Density Fe_3Si Nanodots Epitaxially Grown on Si(111) Substrates Covered with Ultrathin SiO_2 Films. Japanese Journal of Applied Physics, 2011, 50, 015501.	1.5	6
104	Annealing Effects on Ge/ SiO_2 Interface Structure in Wafer-Bonded Germanium-on-Insulator Substrates. Japanese Journal of Applied Physics, 2011, 50, 04DA13.	1.5	6
105	Electrical characterization of wafer-bonded Ge(111)-on-insulator substrates using four-point-probe pseudo-metal-oxide-semiconductor field-effect transistor method. Thin Solid Films, 2012, 520, 3232-3235.	1.8	6
106	Crystalline property analysis of semipolar (20 \times 21) GaN on (22 \times 43) patterned sapphire substrate by X-ray microdiffraction and transmission electron microscopy. Physica Status Solidi (B): Basic Research, 2015, 252, 1149-1154.	1.5	6
107	Phase diagram of the Bi_2O_3 - SrO - CaO quasiternary system. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 1993, 24, 1447-1449.	2.2	5
108	Characterization of semiconductor nanostructures formed by using ultrathin Si oxide technology. Applied Surface Science, 2008, 255, 669-671.	6.1	5

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109	Impact ionization of excitons in Ge/Si structures with Ge quantum dots grown on the oxidized Si(100) surfaces. <i>Journal of Applied Physics</i> , 2014, 115, 203702.	2.5	5
110	Thickness and growth condition dependence of crystallinity in semipolar (20°±21) GaN films grown on (22°±43) patterned sapphire substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1142-1148.	1.5	5
111	Effect of Fe coating of nucleation sites on epitaxial growth of Fe oxide nanocrystals on Si substrates. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 08NB12.	1.5	5
112	Thermoelectric properties of epitaxial FeSi_2 thin films grown on Si(111) substrates with various film qualities. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 05DC04.	1.5	5
113	Growth of epitaxial FeGe_3 nanocrystals with incommensurate Nowotny chimney-ladder phase on Si substrate. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 08NB01.	1.5	5
114	Control of thermoelectric properties in Mn-substituted $\text{Fe}_{1-x}\text{Mn}_x\text{Si}$ epilayers. <i>Physical Review B</i> , 2020, 102, .	2.2	5
115	Annealing Effects on Ge/SiO ₂ Interface Structure in Wafer-Bonded Germanium-on-Insulator Substrates. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DA13.	1.5	5
116	Electrical Characterization of Wafer-Bonded Germanium-on-Insulator Substrates Using a Four-Point-Probe Pseudo-Metal-Oxide Semiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DA14.	1.5	5
117	Starin dependent electrical resistance of carbon-insulator composite. <i>Journal of Materials Science Letters</i> , 1994, 13, 829-831.	0.5	4
118	Spatially Extended Polymerization of C ₆₀ Clusters Induced by Localized Current Injection from Scanning Tunneling Microscope Tips. <i>Molecular Crystals and Liquid Crystals</i> , 2002, 386, 135-138.	0.9	4
119	Role of Intermolecular Separation in Nanoscale Patterning C ₆₀ Films by Local Injection of Electrons from Scanning Tunneling Microscope Tip. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L1373-L1376.	1.5	4
120	Giant fullerenes formed on C ₆₀ films irradiated with electrons field-emitted from scanning tunneling microscope tips. <i>Applied Surface Science</i> , 2008, 254, 7881-7884.	6.1	4
121	High resolution transmission electron microscopy study of iron-silicide nanodot structures grown on faintly oxidized Si (111) surfaces. <i>Thin Solid Films</i> , 2009, 517, 2865-2870.	1.8	4
122	X-ray microdiffraction investigation of crystallinity and strain relaxation in Ge thin lines selectively grown on Si(001) substrates. <i>Solid-State Electronics</i> , 2011, 60, 26-30.	1.4	4
123	Characterization of Ge Films on Si(001) Substrates Grown by Nanocontact Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 095503.	1.5	4
124	Self-assembly of Ge clusters on highly oriented pyrolytic graphite surfaces. <i>Surface Science</i> , 2014, 628, 82-85.	1.9	4
125	Nanostructural effect on thermoelectric properties in Si films containing iron silicide nanodots. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SFFB01.	1.5	4
126	Anomalous Enhancement of IR Emission in $\text{Zn}_{1-x}\text{Mn}_x\text{S}$ Retrieved after Pressure-Induced Phase Transition. <i>Physica Status Solidi (B): Basic Research</i> , 1999, 211, 359-364.	1.5	3

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127	The enhanced signal of subgap centers in tip-probing photoabsorption spectroscopy with an assist of a subsidiary light. <i>Journal of Applied Physics</i> , 2008, 103, 044303.	2.5	3
128	Conductive optical-fiber STM probe for local excitation and collection of cathodoluminescence at semiconductor surfaces. <i>Optics Express</i> , 2013, 21, 19261.	3.4	3
129	Investigating the origin of intense photoluminescence in Si capping layer on Ge _{1-x} Sn _x nanodots by transmission electron microscopy. <i>Journal of Applied Physics</i> , 2013, 113, 074302.	2.5	3
130	Anisotropic crystalline morphology of epitaxial thick AlN films grown on triangular-striped AlN/sapphire template. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 731-735.	1.8	3
131	Formation and optical properties of Ge films grown on Si(111) substrates using nanocontact epitaxy. <i>Applied Surface Science</i> , 2015, 325, 170-174.	6.1	3
132	Amorphous/epitaxial superlattice for thermoelectric application. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 081201.	1.5	3
133	Protosymbol emergence based on embodiment: robot experiments. , 0, , .		2
134	Structural Analysis of Si-Based Nanodot Arrays Self-Organized by Selective Etching of SiGe/Si Films. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 08LB11.	1.5	2
135	Self-organization of two-dimensional SiGe nanodot arrays using selective etching of pure-edge dislocation network. <i>Journal of Applied Physics</i> , 2011, 109, 044301-044301-4.	2.5	2
136	Areal density control of ZnO nanowires in physical vapor transport using Ge nanocrystals. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 08NB07.	1.5	2
137	Modulation of lattice constants by changing the composition and strain in incommensurate Nowotny chimney-ladder phase FeGe epitaxially grown on Si. <i>Surface Science</i> , 2019, 690, 121470.	1.9	2
138	Semiconductor Nanostructure Design for Thermoelectric Property Control. <i>International Journal of Nanoscience</i> , 2019, 18, 1940036.	0.7	2
139	Formation of Silicon Quantum Dots Sheet on a Nonmetallic CaF ₂ Surface. <i>Advanced Materials Interfaces</i> , 2020, 7, 2001295.	3.7	2
140	Direct mapping of temperature-difference-induced potential variation under non-thermal equilibrium. <i>Applied Physics Letters</i> , 2021, 118, 091605.	3.3	2
141	Synergistic phonon scattering in epitaxial silicon multilayers with germanium nanodot inclusions. <i>Physical Review B</i> , 2021, 104, .	3.2	2
142	The Effect of Ethanol on Disassembly of Amyloid- β 1-42 Pentamer Revealed by Atomic Force Microscopy and Gel Electrophoresis. <i>International Journal of Molecular Sciences</i> , 2022, 23, 889.	4.1	2
143	Seed-assisted epitaxy of intermetallic compounds with interface-determined orientation: Incommensurate Nowotny chimney-ladder FeGe epitaxial film. <i>Acta Materialia</i> , 2022, 236, 118130.	7.9	2
144	Title is missing!. <i>Journal of Materials Science Letters</i> , 1999, 18, 1159-1161.	0.5	1

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145	STM observations of photo-induced jumps of chlorine atoms chemisorbed on Si(111)-(7 \times 7) surface. <i>Surface Science</i> , 2005, 593, 155-160.	1.9	1
146	X-ray Microdiffraction Study on Crystallinity of Micron-Sized Ge Films Selectively Grown on Si(001) Substrates. <i>ECS Transactions</i> , 2010, 33, 887-892.	0.5	1
147	Microscopic Structure of Directly Bonded Silicon Substrates. <i>Key Engineering Materials</i> , 0, 470, 164-170.	0.4	1
148	Scanning tunneling microscope-based local electroluminescence spectroscopy of p-AlGaAs/i-GaAs/n-AlGaAs double heterostructure. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012, 30, 021802.	1.2	1
149	(Invited) GOI Substrates: Fabrication and Characterization. <i>ECS Transactions</i> , 2013, 50, 709-725.	0.5	1
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